

Phase Control SCR

Part Number (24)			V _{RRM} V _{DRM} (V)	I _O (DC)@T _C (A) (°C)		I _{TSM} (2) 50 Hz 60 Hz (A)		V _{TM} (V)	(15) R _{thJC} DC (°C/W)	Fax-on-Demand Number	Case Style, (Case Outline) (1)
Negative	Positive	Positive									
Three-phase Controlled Bridges											
51MT80K	52MT80K	53MT80K	800	55	85	330	345	2.68	0.179	87113	INT-A-Pak (B13)
51MT100K	52MT100K	53MT100K	1000	55	85	330	345	2.68	0.179	87113	
51MT120K	52MT120K	53MT120K	1200	55	85	330	345	2.68	0.179	87113	
51MT140K	52MT140K	53MT140K	1400	55	85	330	345	2.68	0.179	87113	
51MT160K	52MT160K	53MT160K	1600	55	85	330	345	2.68	0.179	87113	
91MT80K	92MT80K	93MT80K	800	90	85	800	840	1.65	0.144	87113	
91MT100K	92MT100K	93MT100K	1000	90	85	800	840	1.65	0.144	87113	
91MT120K	92MT120K	93MT120K	1200	90	85	800	840	1.65	0.144	87113	
91MT140K	92MT140K	93MT140K	1400	90	85	800	840	1.65	0.144	87113	
91MT160K	92MT160K	93MT160K	1600	90	85	800	840	1.65	0.144	87113	
111MT80K	112MT80K	113MT80K	800	110	95	950	1000	1.57	0.117	87113	
111MT100K	112MT100K	113MT100K	1000	110	95	950	1000	1.57	0.117	87113	
111MT120K	112MT120K	113MT120K	1200	110	95	950	1000	1.57	0.117	87113	
111MT140K	112MT140K	113MT140K	1400	110	95	950	1000	1.57	0.117	87113	
111MT160K	112MT160K	113MT160K	1600	110	95	950	1000	1.57	0.117	87113	

Glassvated Thyristor Die

Die Part No.	Side (25)		V _{RRM} (V)	Passivation	Metallization	Gate Location	Quantity Per Carrier	Equivalent Device Series
	Dimensions (1) (inches)	I _T (AV) (A)						
Solderable Type								
IR180SG08G	0.180	20	800	Glass	Anode= Gold	Corner	256	
IR180SG12G	0.180	20	1200		Cathode= Gold		256	
IR210SG08G	0.210	25	800	Glass	Anode= Gold	Center	196	
IR210SG12G	0.210	25	1200		Cathode= Gold		196	
IR230SG08G	0.230	25	800	Glass	Anode= Gold	Corner	196	P100, P400
IR230SG12G	0.230	25	1200		Cathode= Gold		196	
IR350SG08G	0.350	55	800	Glass	Anode= Gold	Center	100	50RIA, T50RIA, T70RIA
IR350SG12G	0.350	55	1200		Cathode= Gold		100	
IR480SG08G	0.480	90	800	Glass	Anode= Gold	Corner	49	T90RIA
IR480SG12G	0.480	90	1200		Cathode= Gold		49	

Die Part No.	Side (25)		V _{RRM} (V)	Passivation	Metallization	Gate Location	Quantity Per Carrier	Equivalent Device Series
	Dimensions (1) (inches)	I _T (AV) (A)						
Bondable Type								
IR250BG08D	0.245	25	800	Glass	Anode= Silver	Center	190	IRKT26/08
IR250BG12D	0.245	25	1200		Cathode= Aluminum		190	IRKT26/12
IR370BG08D	0.365	55	800	Glass	Anode= Silver	Center	100	IRKT56/08
IR370BG12D	0.365	55	1200		Cathode= Aluminum		100	IRKT56/12
IR485BG08D	0.480	90	800	Glass	Anode= Silver	Corner	49	IRKT91/08
IR485BG12D	0.480	90	1200		Cathode= Aluminum		49	IRKT91/12

- (1) See page 105 for Case Outline information
- (2) 100% V_{RRM} re-applied @ T_j = T_j max 125°C
- (15) Value given for R_{thJC} is per module, DC operation.
- (23) @ I_PPeak = 150A, T_j = 25°C
- (24) RMS isolation voltage = 4000V - 50Hz.
- (25) Values strongly dependent on assembly technique

